EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(planar near dielectric) same (metal near layer) same (maximum near1 spacing) same (oxide near layer) same (("teos-based" near procedure) (teos near based near procedure)) same (("facet-etching" (facet near etching)) near2 (oxide near layer)) same ((deposition near rate) with (less higher fewer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:03
L2	6332	438/584,595,645,646,656,689, 758.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:03
L3	3	(planar near dielectric) same (metal near layer) same (oxide near layer) same (("teos-based" near procedure) (teos near based near procedure)) same (("facet-etching" (facet near etching)) near2 (oxide near layer)) same ((deposition near rate) with (less higher fewer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:04
L4	3	(metal near layer) same (oxide near layer) same (("teos-based" near procedure) (teos near based near procedure)) same (("facet-etching" (facet near etching)) near2 (oxide near layer)) same ((deposition near rate) with (less higher fewer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:05
L5	3	(metal near layer) same (oxide near layer) same ("teos-based" (teos near based) (teos near1 procedure)) same ("facet-etching" (facet near etching)) same ((deposition near rate) with (less higher fewer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:07
L6	3	("teos-based" (teos near based) (teos near1 procedure)) same ("facet-etching" (facet near etching)) same ((deposition near rate) with (less higher fewer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:07

EAST Search History

L7	692	("teos-based" (teos near based) (teos near1 procedure))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:07
L8	19	2 and 7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/20 18:07